TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT6L61AE

VHF-UHF Band Low Noise Amplifier Application

VHF-UHF Band Oscillator Application

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating		Unit	
		Q1	Q2	Onit	
Collector-base voltage	V _{CBO}	10	10	V	
Collector-emitter voltage	V _{CEO}	5	5	V	
Emitter-base voltage	V _{EBO}	1.5	2	V	
Collector current	۱ _C	25	40	mA	
Base current	Ι _Β	10	10	mA	
Collector power dissipation	P _C	100		mW	
	(Note1)				
Junction temperature	Tj	125		°C	
Storage temperature range	T _{stg}	-55~125		°C	

Note1: Total power dissipation of Q1 and Q2

	Q1	Q2
Three pin SSM type part No.	MT3S07S	MT3S04AS



Weight: 3 mg (typ.)

Unit: mm

Electrical Characteristics Q1-Side (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current	I _{CBO}	$V_{CB} = 5 \text{ V}, \text{ I}_{E} = 0$			0.1	μA	
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 V, I_{C} = 0$		_	1	μA	
DC current gain	h _{FE}	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	70	_	140	_	
Transition frequency	f _T	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 10 \text{ mA}$	10	12		GHz	
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$		7		dB	
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 15 \text{ mA}, \text{ f} = 2 \text{ GHz}$	6.5	8.5			
Noise figure	NF (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$		1.6	3	dB	
	NF (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 2 \text{ GHz}$		1.5	3		
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$ (Note2)	—	0.45	0.85	pF	

Electrical Characteristics Q2-Side (Ta = 25°C)

Characteristics	Symbol	Test Condition		Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 5 V, I_E = 0$			0.1	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 V, I_C = 0$			1	μA
DC current gain	h _{FE}	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$			160	
Transition frequency	f _T (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}$	2	4.5		GHz
	f _T (2)	$V_{CE} = 3 V, I_C = 7 mA$	5	7		
Insertion gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, \text{ I}_{C} = 5 \text{ mA}, \text{ f} = 1 \text{ GHz}$	_	8.5		dB
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, \text{ I}_{C} = 20 \text{ mA}, \text{ f} = 1 \text{ GHz}$	7.5	11		
Noise figure	NF (1)	V _{CE} = 1 V, I _C = 5 mA, f = 1 GHz		1.3	2.2	dB
	NF (2)	V _{CE} = 3 V, I _C = 7 mA, f = 1 GHz	_	1.2	2	
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz} \tag{Note2}$		0.9	1.25	pF

Note2: Cre is measured by 3 terminal method with capacitance bridge.

Marking



Pin Assignment (top view)



Caution

This device electrostatic sensitivity. Please handle with caution.

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